Trench FS IGBT

Features

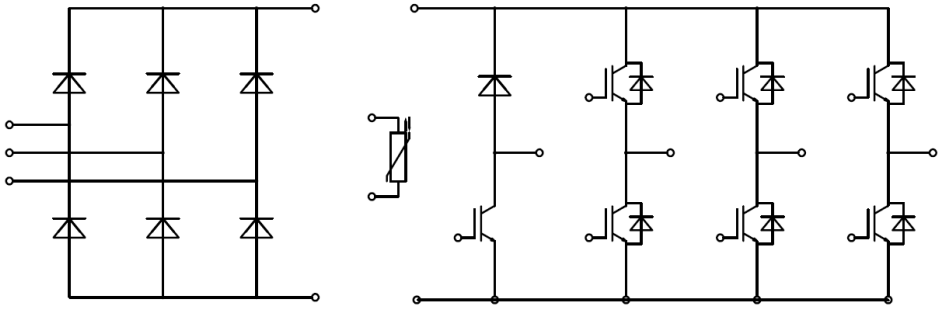
- High Power Density
- High mechanical robustness
- Compact design
- Isolated heatsink using DBC technology
- Very low forward voltage drop
- Fast & soft reverse recovery anti-parallel FWD

Applications

- Active Rectifier
- Air Conditioning
- Motor Drives

Product Summary

Parameter	Value	Unit
V_{CES}	1200	V
I_C(@ T_C= 100℃)	50	A
I_{CRM}(@ t_P= 1ms)	100	A
$V_{CE(sat)}$(Typ)	1.80	V



IGBT, Inverter Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1200	V
Gate-emitter peak voltage		V_{GES}	±20	V
Continuous collector current	T_C = 100°C, T_{vj} = 175°C	$I_{C\ nom}$	50	A
Repetitive peak collector current	t_P = 1ms	I_{CRM}	100	A

IGBT, Inverter Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions		Symbol	Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	I_C = 50A, V_{GE} = 15V	T_{vj} = 25°C	$V_{CE(sat)}$		1.80	2.25	V
		T_{vj} = 125°C			2.15		
Gate threshold voltage	V_{CE}=V_{GE}, I_C=1.0mA		$V_{GE(th)}$	5.2	5.8	6.4	V
Gate-emitter leakage current	V_{CE} = 0V, V_{GE} = 20V		I_{GES}			400	nA
Collector leakage current	V_{CE}=1200V，V_{GE}=0V		I_{CES}			1	mA
Input capacitance	f = 1MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		4.42		nF
Output capacitance			C_{oes}		0.04		nF
Gate charge	V_{GE} = -15V…+15V		Q_G		0.32		uC
Turn-on delay time, inductive load	V_{CE} = 600V, I_C = 50A, R_G = 15Ω V_{GE} = ±15V, T_{vj} = 25℃		$t_{d(on)}$		129		ns
Rise time, inductive load			t_r		85		ns
Turn-off delay time, inductive load			$t_{d(off)}$		213		ns
Fall time, inductive load			t_f		125		ns
Turn-on energy loss per pulse			E_{on}		5.18		mJ
Turn-off energy loss per pulse			E_{off}		3.10		mJ
Turn-on delay time, inductive load	V_{CE} = 600V, I_C = 50A, R_G =15Ω, V_{GE} = ±15V, T_{vj} = 125℃		$t_{d(on)}$		129		ns
Rise time, inductive load			t_r		99		ns
Turn-off delay time, inductive load			$t_{d(off)}$		226		ns
Fall time, inductive load			t_f		192		ns
Turn-on energy loss per pulse			E_{on}		8.08		mJ
Turn-off energy loss per pulse			E_{off}		3.98		mJ
SC data	tp≤10us， V_{GE}≤15V， V_{CC}=800V,V_{CEM}≤1200V, T_{vj}=125℃		I_{SC}		150		A
Thermal resistance, junction to case	per IGBT		$R_{th(j-c)}$		0.60	0.70	℃/W
Temperature under switching conditions			$T_{vj\ op}$	-40		150	℃

FRED, Inverter Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1200	V
Continuous DC forward current		I_F	50	A
Repetitive peak forward current	t_P = 1ms	I_{FRM}	100	A
I^2t value for fusing	t = 10ms, V_R = 0V, T_{vj} =150℃,	I^2t	220	A^2s

FRED, Inverter Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions		Symbol	Values			Unit
				Min.	Typ.	Max.	
Forward voltage	I_F = 50A, V_{GE} = 0V	T_{vj} = 25°C	V_F		2.10	2.40	V
		T_{vj} = 125°C			1.80		
Peak reverse recovery current	I_F = 50A, di/dt = 400A/μs, V_R = 600V, V_{GE} = -15V	T_{vj} = 25°C	I_{RM}		16		A
		T_{vj} = 125°C			24		
Recovered charge		T_{vj} = 25°C	Q_{rr}		1.79		μC
		T_{vj} = 125°C			5.23		
Peak reverse recovery energy		T_{vj} = 25°C	Erec		0.52		mJ
		T_{vj} = 125°C			1.53		
Thermal resistance, junction to case	per diode		$R_{th(j-c)}$		0.80	0.90	K/W
Temperature under switching conditions			$T_{vj\ op}$	-40		150	℃

Diode, Rectifier Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1600	V
Maximum RMS forward current per chip	T_C = 80°C	I_{FRMSM}	50	A
Maximum RMS current at rectifier output	T_C = 80°C	I_{RMSM}	50	A
Repetitive peak forward current	t_P = 10 ms, T_{vj} = 25°C	I_{FSM}	450	A
I^2t value for fusing	t_P = 10 ms, T_{vj} = 25°C	I^2t	1000	A^2s

Diode, Rectifier Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	T_{vj} = 150°C, I_F=50A	V_F		1.20		V
Reverse current	T_{vj} = 150°C, V_R=1600V	I_R		2.0		mA
Thermal resistance, junction to case	per diode	$R_{th(j-c)}$		1.05	1.15	K/W
Temperature under switching conditions		$T_{vj\ op}$	-40		150	℃

IGBT, Brake-Chopper Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1200	V
Gate-emitter peak voltage		V_{GES}	±20	V
Continuous collector current	T_C = 100°C, T_{vj} = 175°C	$I_{C\ nom}$	40	A
Repetitive peak collector current	t_P = 1ms	I_{CRM}	80	A

IGBT, Brake-Chopper Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions		Symbol	Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	I_C = 40A, V_{GE} = 15V	T_{vj} = 25°C	$V_{CE(sat)}$		1.80	2.10	V
		T_{vj} = 125°C			2.25		
Gate threshold voltage	V_{CE}=V_{GE}, I_C=0.50mA，		$V_{GE(th)}$	5.2	5.8	6.4	V
Gate-emitter leakage current	V_{CE} = 0V, V_{GE} = 20V		I_{GES}			400	nA
Collector leakage current	V_{CE}=1200V， V_{GE}=0V		I_{CES}			1.0	mA
Input capacitance	f = 1MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		2.08		nF
Output capacitance			C_{oes}		0.02		nF
Gate charge	V_{GE} = -15V…+15V		Q_G		0.12		uC
Turn-on delay time, inductive load	V_{CC} = 600V, I_C = 40A, R_G = 37Ω, V_{GE} = ±15V, T_{vj} = 25℃		$t_{d(on)}$		192		ns
Rise time, inductive load			t_r		140		ns
Turn-off delay time, inductive load			$t_{d(off)}$		307		ns
Fall time, inductive load			t_f		65		ns
Turn-on energy loss per pulse			E_{on}		6.35		mJ
Turn-off energy loss per pulse			E_{off}		2.05		mJ
Turn-on delay time, inductive load	V_{CC} = 600V, I_C = 40A, R_G = 37Ω, V_{GE} = ±15V, T_{vj} = 125℃		$t_{d(on)}$		185		ns
Rise time, inductive load			t_r		152		ns
Turn-off delay time, inductive load			$t_{d(off)}$		334		ns
Fall time, inductive load			t_f		89		ns
Turn-on energy loss per pulse			E_{on}		8.51		mJ
Turn-off energy loss per pulse			E_{off}		2.45		mJ
SC data	tp≤10us， V_{GE}≤15V, V_{CE}=800V,V_{CEM}≤1200V, T_{vj}=125℃		I_{SC}		75		A
Thermal resistance, junction to case	per IGBT		$R_{th(j-c)}$		0.60	0.70	K/W
Temperature under switching conditions			$T_{vj\ op}$	-40		150	℃

FRED, Brake-Chopper Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1200	V
Continuous DC forward current		I_F	30	A
Repetitive peak forward current	t_P = 1ms	I_{FRM}	60	A
I^2t value for fusing	T_{vj} =125°C, t_P = 10ms, V_R = 0V	I^2t	16	A^2s

FRED, Brake-Chopper Electrical Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions		Symbol	Values			Unit
				Min.	Typ.	Max.	
Forward voltage	I_F = 30A, V_{GE} = 0V	T_{vj} = 25°C	V_F		2.10	2.40	V
		T_{vj} = 125°C			1.70		
Peak reverse recovery current	I_F = 30A, di/dt = 200A/µs, V_R = 600V, V_{GE} = -15V	T_{vj} = 25°C	I_{RM}		6.39		A
		T_{vj} = 125°C			11.12		
Recovered charge		T_{vj} = 25°C	Q_{rr}		1.17		µC
		T_{vj} = 125°C			3.27		
Peak reverse recovery energy		T_{vj} = 25°C	Erec		0.31		mJ
		T_{vj} = 125°C			0.84		
Thermal resistance, junction to case	per diode		$R_{th(j-c)}$		1.75	1.90	K/W
Temperature under switching conditions			$T_{vj\ op}$	-40		150	℃

NTC-Thermistor Characteristics (@ T_C = 25°C unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	T_C=25℃	R_{25}		5		KΩ
Deviation of R100	T_C = 100°C, R_{100} = 493 Ω	△R/R	-5		5	%
Power dissipation	T_C = 25°C	P_{25}			20	mW
B-value	$R_2 = R_{25} \exp [B25/50(1/T2 - 1/(298,15\ K))]$	$B_{25/50}$		3375		K
B-value	$R_2 = R_{25} \exp [B25/80(1/T2 - 1/(298,15\ K))]$	$B_{25/80}$		3411		K
B-value	$R_2 = R_{25} \exp [B25/100(1/T2 - 1/(298,15\ K))]$	$B_{25/100}$		3433		K

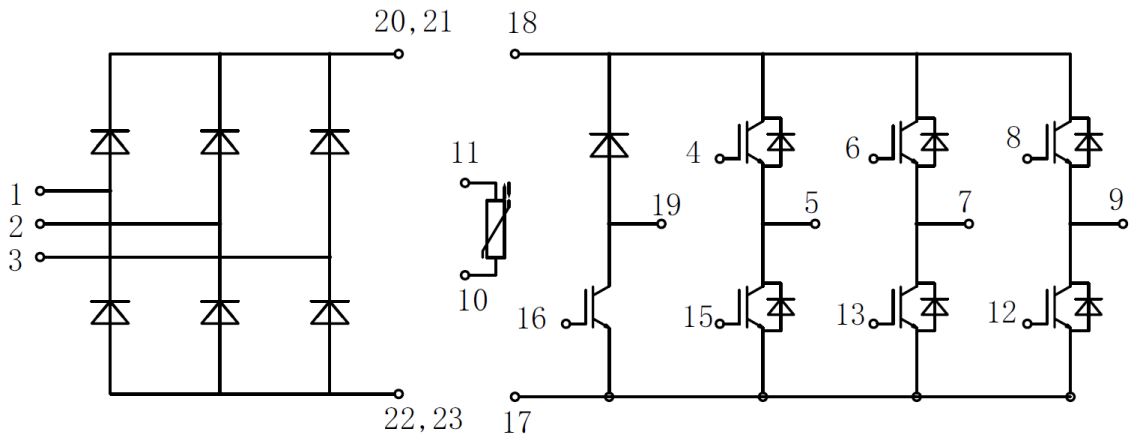
Module Characteristics

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Isolation Voltage (All Terminals Shorted)	RMS, f = 50Hz,1minute	V_{iso}	2.5			KV
Thermal resistance, case to heatsink	per module	$R_{th(c-s)}$		0.009		K/W
Maximum Junction Temperature	Inverter, brake-chopper	$T_{vj\ max}$			175	℃
	rectifier				150	℃
Stray inductance module		L_{SCE}		30		nH
Module lead resistance, terminals - chip	per switch	$R_{CC'+EE'}$		6		mΩ
		$R_{AA'+CC'}$		5		mΩ
Storage Temperature		T_{stg}	-40		125	℃
Mounting force per clamp		F	40		80	N

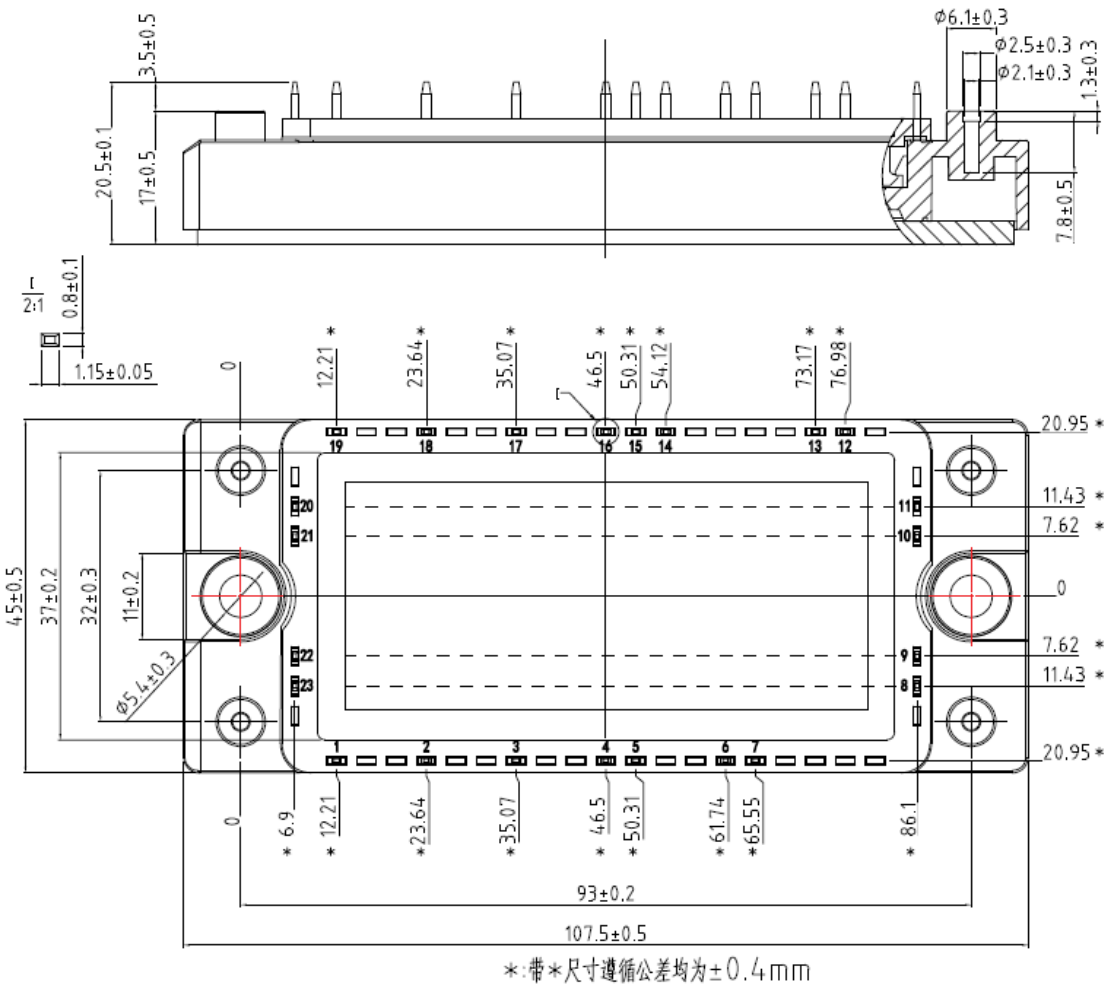
Ordering Information

Device	Marking	Package	Weight	Inner Box	Per Carton
JMG50PM12P2S1	JMG50PM12P2S1	P2	185g/PCS	15PCS	75PCS

Circuit Diagram



Package Outlines (mm)



Unit of measurement: mm

Typical Electrical & Thermal Characteristics

Fig 1. IGBT Output Characteristics,
Inverter(typical) VGE=15 V

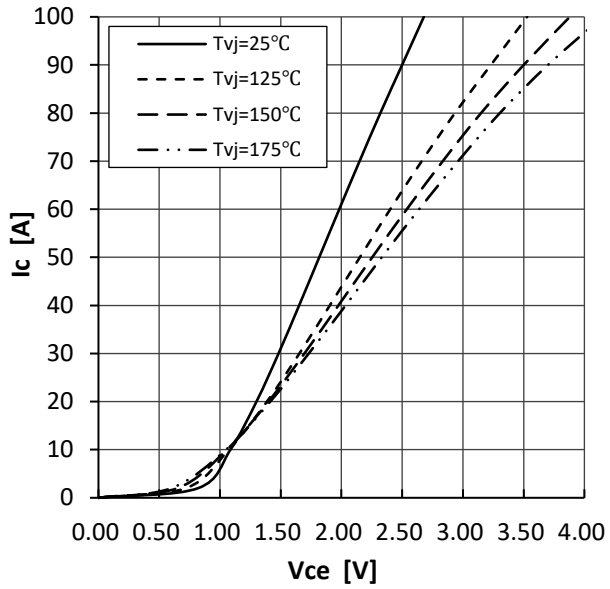


Fig 2. IGBT Output Characteristics,
Inverter(typical)

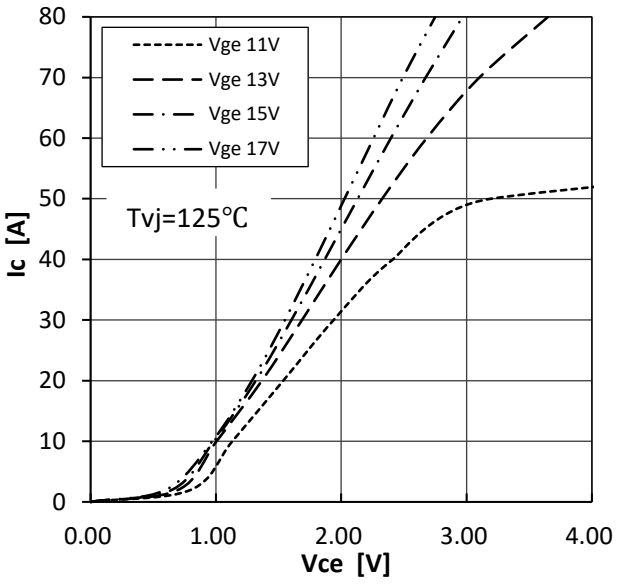


Fig 3. IGBT Switching Loss vs. Ic,
Inverter(typical)
Rg=15 Ω, VCE=600 V, VGE=±15 V

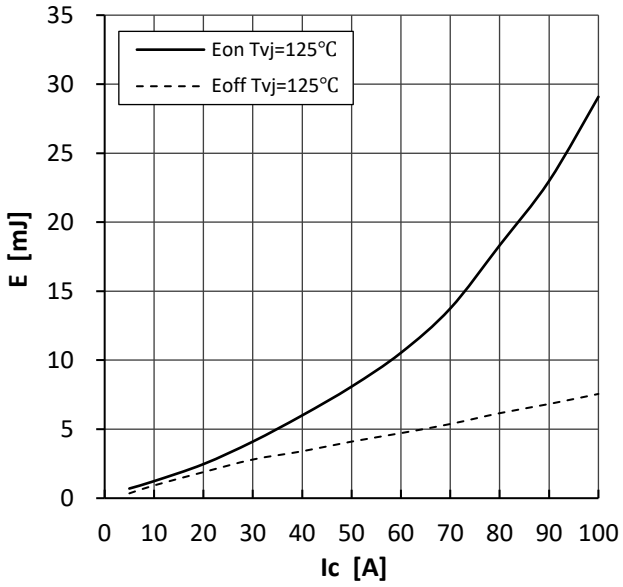


Fig 4. IGBT Switching Loss vs. Rg,
Inverter(typical)
Ic=50 A, VCE=600 V, VGE=±15 V

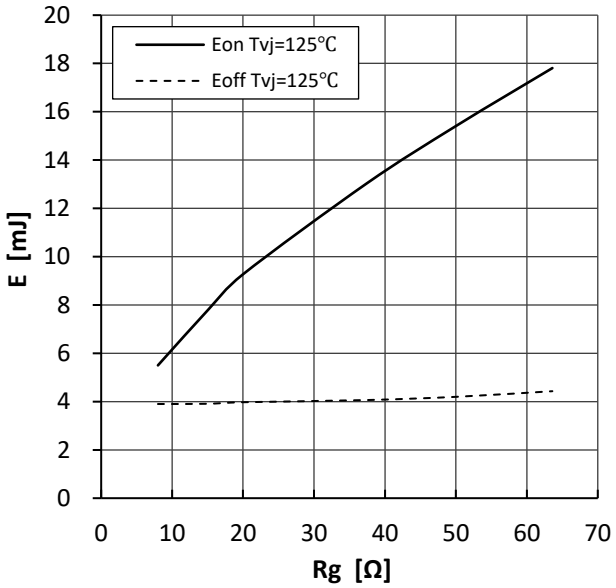


Fig 5. Reverse bias safe operating area,
IGBT, Inverter(RBSOA)

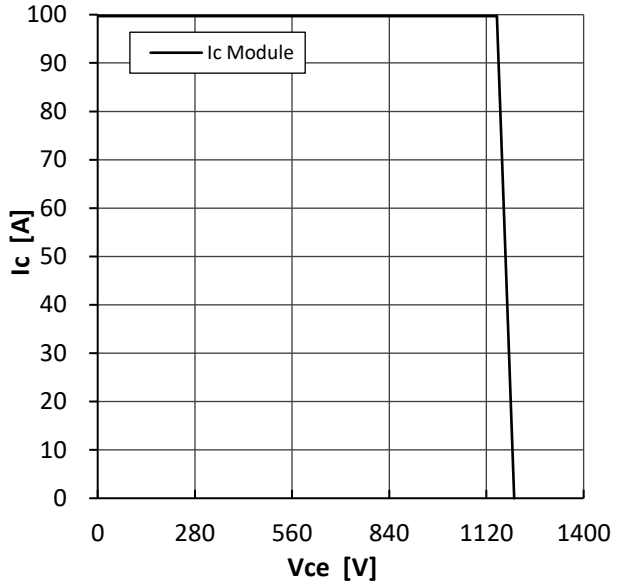


Fig 6. FRED Forward Characteristics,
Inverter(typcial)

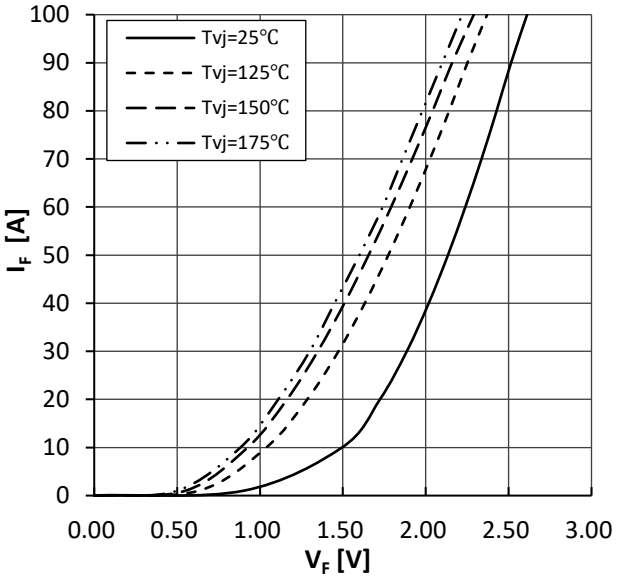


Fig 7. FRED FRED Switching Loss vs. Ic,
Inverter(typcial)
Rg=15 Ω, VCE=600 V

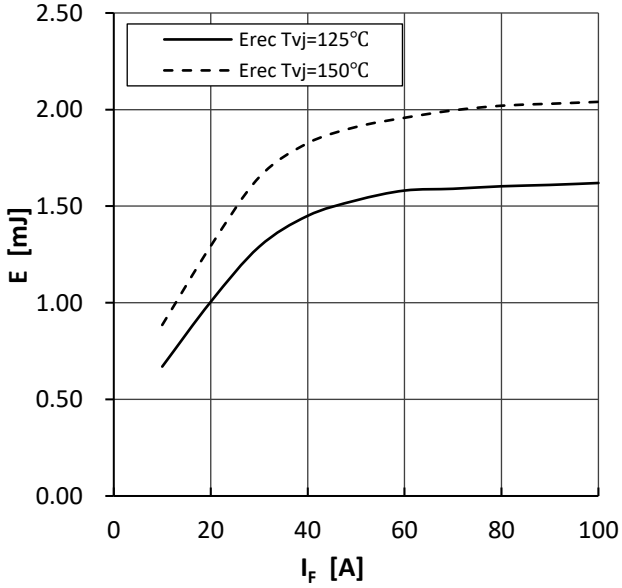


Fig 8. FRED Switching Loss vs. Rg,
Inverter(typcial)
Ic=50 A, VCE=600 V

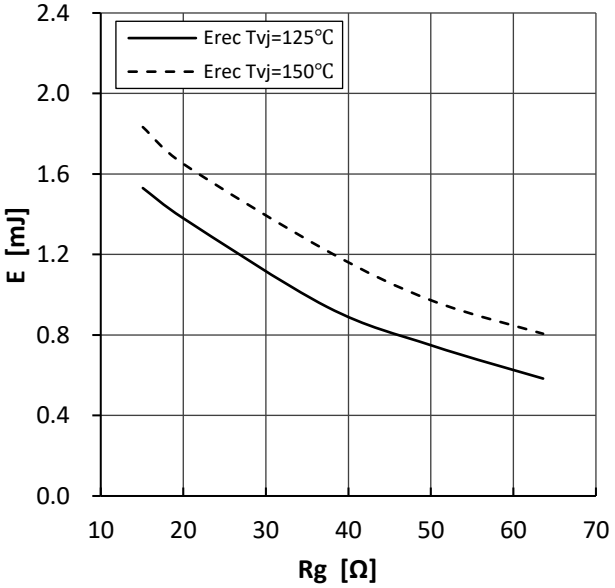
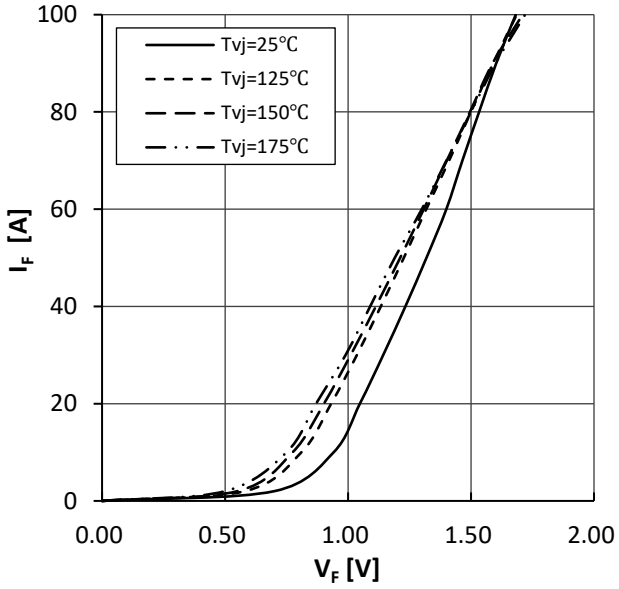


Fig 9. Diode Rectifier Forward Characteristics



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